# SGM48522 Dual 5V, 7A/6A Low-side GaN and MOSFET Driver

## GENERAL DESCRIPTION

The high-speed, dual-channel low-side driver SGM48522 is designed to drive GaN FETs and logic level MOSFETs. The application areas include LiDAR, time of flight, facial recognition, and power converters using low-side drivers. The SGM48522 provides 7A source and 6A sink output current capability. Split output configuration allows individual turn-on and turn-off time optimization depending on FET. The Flip-Chip TQFN package and pinout minimize parasitic inductances to reduce the rise and fall time and limit the ringing. Additionally, the 2ns propagation delay with minimized tolerances and variations allows efficient operation at high frequencies.

The driver has internal under-voltage lockout and over-temperature protection against overload and fault events.

The SGM48522 is available in a Green TQFN-2×2-10BL package.

# **FEATURES**

- 5V Supply Voltage
- 7A Peak Source and 6A Peak Sink Currents
- Ultra-Fast, Low-side Gate Driver for GaN and Si FETs
- Minimum Input Pulse Width: 1ns
- Up to 60MHz Operation
- Propagation Delay: 2ns (TYP)
- Rise Time: 750ps (TYP)
- Fall Time: 560ps (TYP)
- Protection Features:
  - Under-Voltage Lockout (UVLO)
  - Over-Temperature Protection (OTP)
- Available in a Green TQFN-2×2-10BL Package

# **APPLICATIONS**

Laser Distance Measuring System (LiDAR)
5G RF Communication System
Wireless Charging System
GaN DC/DC Conversion System

## TYPICAL APPLICATION

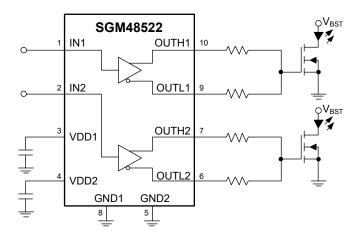


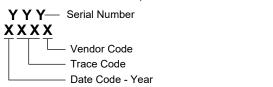
Figure 1. Typical Application Circuit

## PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM48522	TQFN-2×2-10BL	-40°C to +125°C	SGM48522XTSW10G/TR	061 XXXX	Tape and Reel, 3000

#### MARKING INFORMATION

NOTE: XXXX = Date Code, Trace Code and Vendor Code.



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

#### **ABSOLUTE MAXIMUM RATINGS**

Supply Voltage, V <sub>DD1</sub> , V <sub>DD2</sub> 0.3V to 6V
IN1, IN2 Pin Voltage, V <sub>INx</sub> 0.3V to 6V
OUTH1, OUTH2 Pin Voltage, $V_{OUTHx}$ 0.3V to $V_{DD}$ + 0.3V
OUTL1, OUTL2 Pin Voltage, V <sub>OUTLx</sub>
DC0.3V to 6V
Repetitive Pulse < 5ns2V to 7V
Package Thermal Resistance
TQFN-2×2-10BL, θ <sub>JA</sub> 81.8°C/W
Junction Temperature+150°C
Storage Temperature Range65°C to +150°C
Lead Temperature (Soldering, 10s)+260°C
ESD Susceptibility
HBM4000V
CDM1500V

#### RECOMMENDED OPERATING CONDITIONS

Supply Voltage, V <sub>DD1</sub> , V <sub>DD2</sub>	4.5V to 5.5V
IN1, IN2 Pin Voltage, V <sub>INx</sub>	0V to 5.5V
Operating Ambient Temperature Ran	ge40°C to +125°C

#### **OVERSTRESS CAUTION**

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

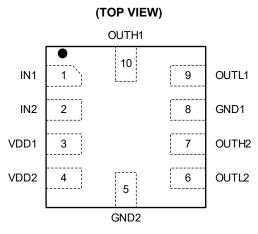
#### **ESD SENSITIVITY CAUTION**

This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

#### **DISCLAIMER**

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

# **PIN CONFIGURATION**



TQFN-2×2-10BL

# **PIN DESCRIPTION**

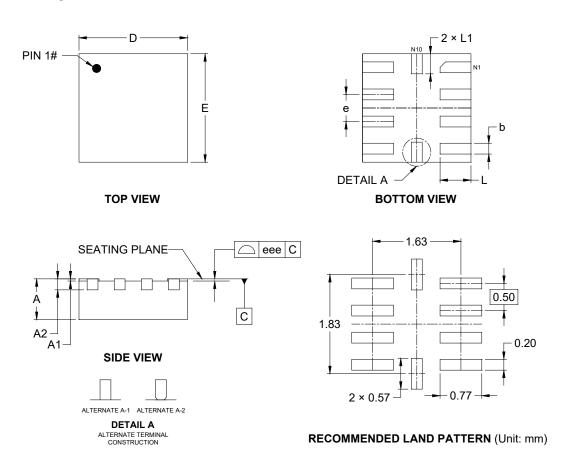
PIN	NAME	I/O	FUNCTION	
1	IN1	I	Channel 1 Control Logic Input (Non-Inverting).	
2	IN2	I	Channel 2 Control Logic Input (Non-Inverting).	
3	VDD1	I	Channel 1 Input Voltage Supply. Bypass to GND with a low inductance ceramic capacitor.	
4	VDD2	I	Channel 2 Input Voltage Supply. Bypass to GND with a low inductance ceramic capacitor.	
5	GND2	_	Channel 2 Ground. Internally connected to GND1 by anti-parallel diodes.	
6	OUTL2	0	Channel 2 Pull-Down Gate Drive Output. Connect it to the gate of the target transistor with an optional resistor.	
7	OUTH2	0	Channel 2 Pull-Up Gate Drive Output. Connect it to the gate of the target transistor with an optional resistor. Internally connected to GND2 by anti-parallel diodes.	
8	GND1	_	Channel 1 Ground.	
9	OUTL1	0	Channel 1 Pull-Down Gate Drive Output. Connect it to the gate of the target transistor with an optional resistor.	
10	OUTH1	0	Channel 1 Pull-Up Gate Drive Output. Connect it to the gate of the target transistor with an optional resistor.	

NOTE: I = input, O = output.

# **FUNCTION TABLE**

INx Pin	OUTHx Pin	OUTLx Pin
L	Open	L
Н	Н	Open

# PACKAGE OUTLINE DIMENSIONS TQFN-2×2-10BL

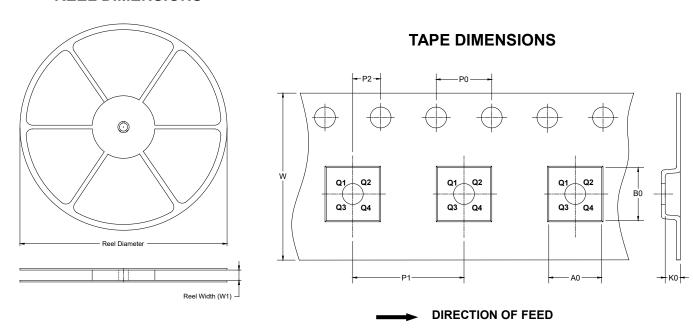


Symbol	Dimensions In Millimeters						
Symbol	MIN	MOD	MAX				
Α	0.700	-	0.800				
A1	0.000	-	0.050				
A2	0.203 REF						
b	0.150	-	0.250				
D	1.900	-	2.100				
E	1.900	-	2.100				
е	0.500 BSC						
L	0.470	0.670					
L1	0.270	-	0.470				
eee	0.080						

NOTE: This drawing is subject to change without notice.

# TAPE AND REEL INFORMATION

## **REEL DIMENSIONS**

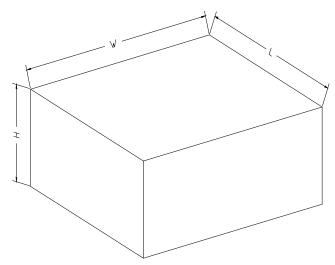


NOTE: The picture is only for reference. Please make the object as the standard.

## **KEY PARAMETER LIST OF TAPE AND REEL**

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
TQFN-2×2-10BL	7"	9.5	2.30	2.30	1.10	4.0	4.0	2.0	8.0	Q1

# **CARTON BOX DIMENSIONS**



NOTE: The picture is only for reference. Please make the object as the standard.

# **KEY PARAMETER LIST OF CARTON BOX**

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
7" (Option)	368	227	224	8
7"	442	410	224	18